Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	155382	(oxide or dielectric or insulating) with substrate with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:09
L2	45269	(oxide or dielectric or insulating) with semiconductor near10 substrate with surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:09
L3	33672	(oxide or dielectric or insulating) near10 semiconductor near10 substrate near10 surface	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:09
L4	7685	((oxide or dielectric or insulating) near10 semiconductor near10 substrate near10 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:10
L5	5747	(((oxide or dielectric or insulating) adj (film or layer)) near10 semiconductor near10 substrate near10 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:10
L6	5375	(((oxide or dielectric or insulating) adj (film or layer)) near10 (semiconductor near5 substrate) near10 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:10
L7	5174	(((oxide or dielectric or insulating) adj (film or layer)) near10 (semiconductor near5 substrate) near5 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:11
L8	4252	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 surface).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:11
L9	35	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 surface near5 apart).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:12

L10	321	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 surface near5 (separate or separated or separation or separating or extend or extending or extended or extension or apart)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:12
L11	1	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 surface near5 (separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 distance).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:13
L12	16	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 surface near5 (separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 distance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:14
L13	5	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 distance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:16
L14	157	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor near5 substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (separate or separated or separation or separating or extend or extending or extended or extension or apart))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:15
L15	5	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 distance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:17

L16	5	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 distance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:19
L17	7	(((oxide or dielectric or insulating) adj (film or layer)) near10 (semiconductor adj substrate) near10 ((first or second or upper or lower or top or bottom) adj surface) near10 (bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near10 distance)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:19
L18	399	(((oxide or dielectric or insulating) adj (film or layer)) near10 (semiconductor adj substrate) near10 ((first or second or upper or lower or top or bottom) adj surface) near10 (bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:19
L19	193	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:19
L20	77	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:21

L21	0	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (implant or implanted or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 (inside near2 substrate)). clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:22
L22	0	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (implant or implanted or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 (inside near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:23
L23	1	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (implant or implanted or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 ((in or inside) near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:23
L24	1	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 ((first or second or upper or lower or top or bottom) adj surface) near5 (implant or implanted or impregnate or impregnating or impregnated or impregnation or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 ((in or inside) near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:24

L25	31	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 (implant or implanted or impregnate or impregnating or impregnated or impregnation or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 ((in or inside) near2 substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:25
L26	2	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 (implant or implanted or impregnate or impregnating or impregnated or impregnation or embed or embedded or embedding or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 ((in or inside) near2 substrate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:26
L27	21	(((oxide or dielectric or insulating) adj (film or layer)) near5 (semiconductor adj substrate) near5 (implant or implanted or impregnate or impregnating or impregnated or impregnation or embed or embedded or embedding or implanting or bury or buried or burying or separate or separated or separation or separating or extend or extending or extended or extension or apart) near5 ((in or inside) near2 substrate)).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:29
L28	8	"5534446"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:30
L29	9	l28 or l27 and (distance or thick or thickness).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:31

L30	5	(I28 or I27) and (distance or thick or thickness).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:32
L31	2	(I28 or I27) and (distance or thick or thickness).clm. and ((buried or embedded or bury or burying or embed or embedding) near2 (oxide or insulating or dielectric))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:32
L32	1	(I28 or I27) and (distance or thick or thickness).clm. and ((buried or embedded or bury or burying or embed or embedding) near2 (oxide or insulating or dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:33
L33	1495	(distance or thick or thickness).clm. and ((buried or embedded or bury or burying or embed or embedding) near2 (oxide or insulating or dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:33
L34	272	(distance or thick or thickness or deep).clm. near10 ((buried or embedded or bury or burying or embed or embedding) near2 (oxide or insulating or dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:33
L35	213	(distance or thick or thickness or deep).clm. near10 ((buried or embedded or bury or burying or embed or embedding) near (oxide or insulating or dielectric)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:33
L37	12	(distance or thick or thickness or deep).clm. near10 ((buried or embedded or bury or burying or embed or embedding) near (oxide or insulating or dielectric) near10 (semiconductor adj substrate)).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:37
L38	12	(distance or thick or thickness or deep).clm. near10 ((buried or embedded or bury or burying or embed or embedding) near (oxide or insulating or dielectric) near10 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:37
L39	116	(distance or thick or thickness or deep) near10 ((buried or embedded or bury or burying or embed or embedding) near (oxide or insulating or dielectric) near10 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:37

L40	116	(distance or thick or thickness or deep) near10 ((buried or embedded or bury or burying or embed or embedding or embedded) near (oxide or insulating or dielectric) near10 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:39
L41	1	(distance or thick or thickness or deep) near10 (continuous or extend or extending or extended or extension) near10 ((buried or embedded or bury or burying or embed or embedding or embedded) near (oxide or insulating or dielectric) near10 (semiconductor adj substrate))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/11/28 18:40